

Photo DMOS-FET Relay

Description

The **LT511** is a miniature 2-Form A solid state relay in an 8 pin DIP package that employs optically coupled MOSFET technology to provide 3750V of input to output isolation. The optically coupled input is controlled by a highly efficient GaAlAs infrared LED and MOS FETs on the output side.

Features

- Low driver power requirements (TTL/CMOS Compatible)
- No moving parts
- High reliability
- Arc-Free with no snubbing circuits
- 3750Vrms Input/Output isolation

Applications

- Telecommunications (PC, Electronic notepad)
- Measuring and Testing equipment
- Industrial control
- Security equipments
- High speed inspection machine

Outline Dimensions

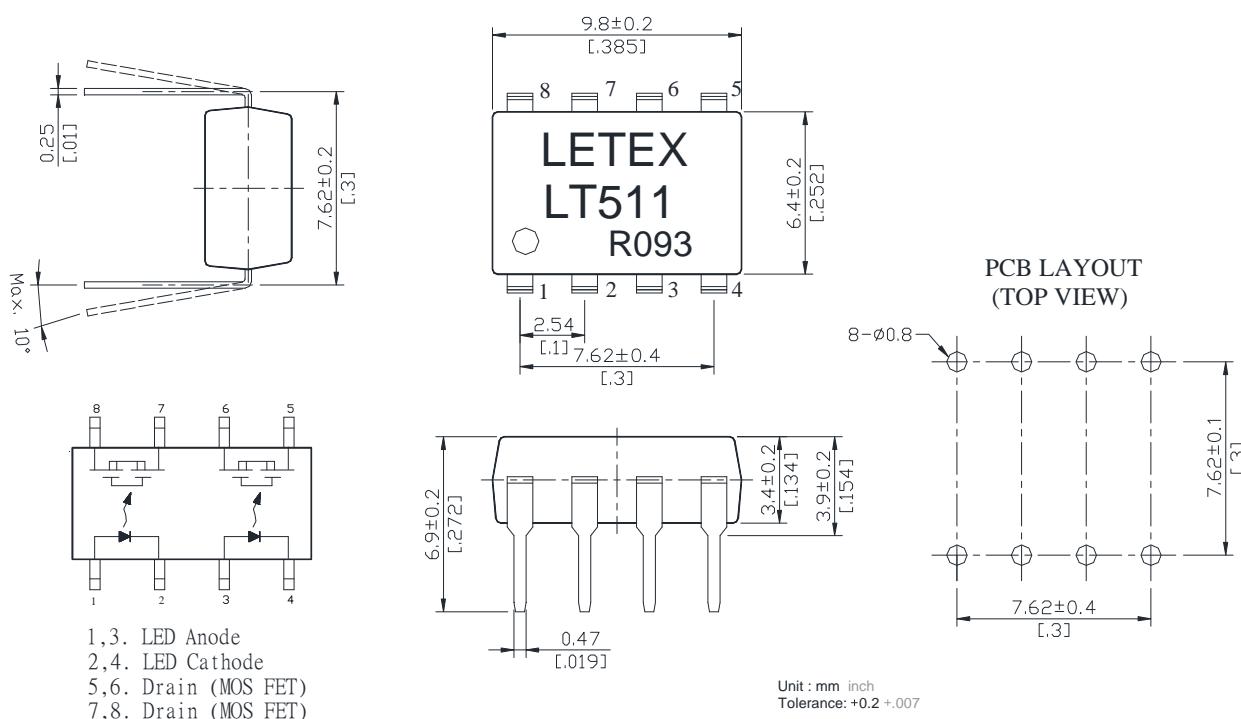


Photo DMOS-FET Relay Specifications

Part Name: LT511

(Load voltage: 350V / Load current: 130mA)

Absolute Maximum Ratings (Ambient Temperature: 25°C)

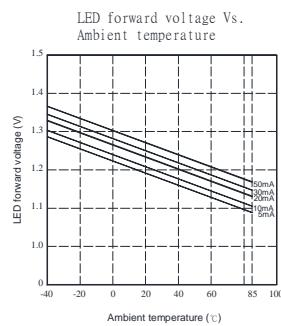
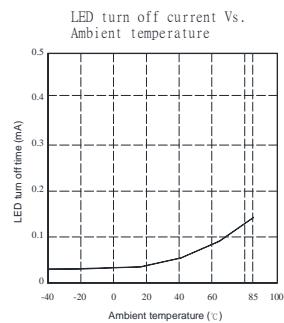
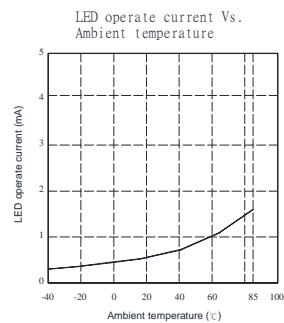
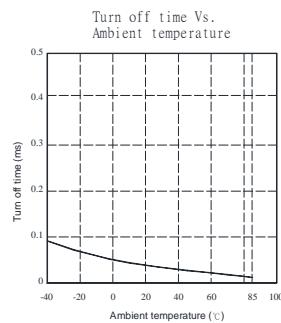
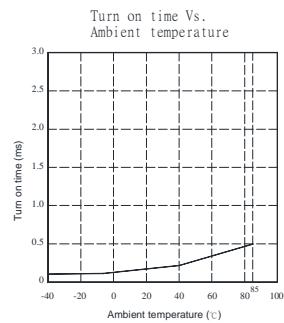
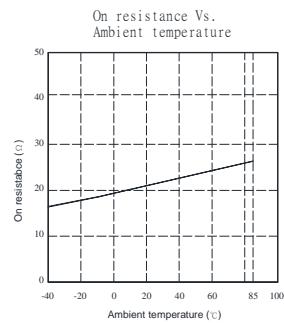
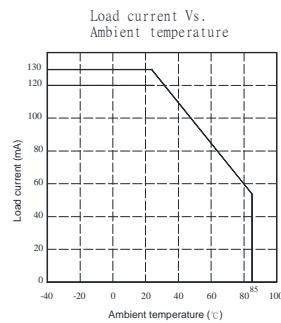
| Item | | Symbol | Value | Units | Note |
|---------------------------|--------------------------|-------------------|-------------|------------------|---------------------|
| Input | Continuous LED Current | I _F | 50 | mA | |
| | Peak LED Current | I _{FP} | 1000 | mA | f=100Hz, duty=1% |
| | LED Reverse Voltage | V _R | 5 | V | |
| | Input Power Dissipation | P _{In} | 75 | mW | |
| Output | Load Voltage | V _L | 350 | V(AC peak or DC) | |
| | Load Current | I _L | 130 | mA | |
| | Peak Load Current | I _{Peak} | 0.6 | A | 100ms(1 pulse) |
| | Output Power Dissipation | P _{out} | 300 | mW | |
| Total Power Dissipation | | P _T | 350 | mW | |
| I/O Breakdown Voltage | | V _{I/O} | 3750 | Vrm | RH=60%, 1min |
| Operating Temperature | | T _{Op} | -40 to +85 | °C | |
| Storage Temperature | | T _{Stg} | -40 to +100 | °C | |
| Pin Soldering Temperature | | T _{Sol} | 260 | °C | 10 sec max. |

Electrical Specifications (Ambient Temperature: 25°C)

| Item | | Symbol | MIN. | TYP. | MAX. | Units | Conditions |
|--------------|---------------------------|--------------------|------------------|------|------|-------|---|
| Input | LED Forward Voltage | V _F | | 1.2 | 1.4 | V | I _F =10mA |
| | Operation LED Current | I _{F On} | | 0.5 | 3.0 | mA | |
| | Recovery LED Current | I _{F Off} | | 0.35 | 0.5 | mA | |
| | Recovery LED Voltage | V _{F Off} | 0.5 | | | V | |
| Output | On-Resistance | R _{On} | | 17 | 24 | Ω | I _F =5mA, I _L =100mA, Time to flow is within 1 sec. |
| | Off-State Leakage Current | I _{Leak} | | | 1 | uA | V _L =Rating |
| | Output Capacitance | C _{out} | | 110 | | pF | V _L =0, f=1MHz |
| Transmission | Turn-On Time | T _{On} | | 0.23 | 0.5 | ms | I _F =5mA, I _L =100mA, |
| | Turn-Off Time | T _{off} | | 0.03 | 0.2 | ms | |
| Coupled | I/O Isolation Resistance | R _{I/O} | 10 ¹⁰ | | | Ω | DC500V |
| | I/O Capacitance | C _{I/O} | | 0.8 | 1.5 | pF | f=1MHz |



Reference Data



Voltage Vs. current characteristics
of output at MOS portion

